EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"ROM" and (semiconductor or wafer or substrate) near4 photoresist and pattern$4 and (ion near4 implant$4) and "LDD" and (organic near4 (spacer or sidewall)) and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 10:31
L2	8	(semiconductor or wafer or substrate) near4 photoresist and pattern$4 and (ion near4 implant$4) and "LDD" and (organic near4 (spacer or sidewall)) and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 11:46
L3	9	(semiconductor or wafer or substrate) near4 photoresist and pattern$4 and (ion near4 implant$4) and "LDD" and ((organic or "ARC" or "BARC") near4 (spacer or sidewall)) and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 12:01
L4	470	(("ARC" or "BARC" or organic) near4 spacer or sidewall) near8 "photoresist pattern"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 12:03
L5	1	(("ARC" or "BARC" or organic) near4 spacer or sidewall) near8 "photoresist pattern" and (semicondcutor or wafer or subsrate) and "LDD" and "HDD" and (ion near4 implant$8) and strip$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 12:06
L6	1	(("ARC" or "BARC" or organic) near4 spacer or sidewall) near8 "photoresist pattern" and (semicondcutor or wafer or subsrate) and "LDD" and "HDD" and (ion near4 implant$8)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 12:06
L7	6	(("ARC" or "BARC" or organic) near4 spacer or sidewall) near8 "photoresist pattern" and (semicondcutor or wafer or subsrate) and "LDD" and (ion near4 implant$8) and strip$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 12:34

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L8	137	(("ARC" or "BARC" or organic) near4 spacer or sidewall) near8 "photoresist pattern" and (semicondcutor or wafer or subsrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:21
L9	16	(("ARC" or "BARC" or organic) near4 spacer or sidewall) near8 "photoresist pattern" and (semicondcutor or wafer or subsrate) and "LDD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 12:46
L10	2	(organic near4 (spacer or sidewall)) near8 "photoresist pattern" and (semicondcutor or wafer or subsrate) and "LDD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 12:54
L11	1	(organic near4 (spacer or sidewall)) near8 "photoresist pattern" and "ROM"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:07
L12	2	(mask near4 "ROM") and "LDD" and organic near4 (sidewall or spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:08
L13	2	(mask near4 "ROM") and "LDD" and (organic near4 (sidewall or spacer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:08
L14	3	(mask near4 "ROM") and "LDD" and ((organic or "BARC" or "ARC")near4 (sidewall or spacer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:12
L15	2	(("ARC" or "BARC" or organic) near4 spacer or sidewall) near8 "photoresist pattern" and (semicondcutor or wafer or subsrate) and (438/257.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/07 13:21

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S1	0	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant$4) and dop$4 and organic and spacer and sidewall and (strip or remov$4) and (pair or two or plurality or multipl$4 or next) same ("ion implant$4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 08:39
S2	55	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant$4) and dop$4 and organic and spacer and sidewall and (strip or remov$4) and (pair or two or plurality or multipl$4 or next) same implant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 10:04
S3	0	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant$4) and dop$4 and organic and spacer and sidewall and (strip or remov$4) and (pair or two or plurality or multipl$4 or next) same implant and (anneal or heat or thermal or cur$4) and (UV or ultra-violet or "ultra violet") and (LDD or "lightly doped drain") and N+ and BARC and "dry etch$4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 08:42
S4	15	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant$4) and dop$4 and organic and spacer and sidewall and (strip or remov$4) and (pair or two or plurality or multipl$4 or next) same implant and (anneal or heat or thermal or cur$4) and (UV or ultra-violet or "ultra violet")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 09:46
S5	3	(wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant$4) and dop$4 and organic and spacer and sidewall and (strip or remov$4) and (pair or two or plurality or multipl$4 or next) same implant and (anneal or heat or thermal or cur$4) and (UV or ultra-violet or "ultra violet") and LDD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 09:42

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| S6 | 0 | (wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant$4) and dop$4 and organic and spacer and sidewall and (strip or remov$4) and (pair or two or plurality or multipl$4 or next) same implant and (anneal or heat or thermal or cur$4) and (UV or ultra-violet or "ultra violet") and LDD and BARC | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/05 08:43 |
| S7 | 1 | (wafer or semiconductor or substrate) and photoresist and pattern and (ion near implant$4) and dop$4 and organic and spacer and sidewall and (strip or remov$4) and (pair or two or plurality or multipl$4 or next) same implant and (anneal or heat or thermal or cur$4) and (UV or ultra-violet or "ultra violet") and LDD and N+ | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/08/05 08:44 |